

Ultra-broadband strong light absorption based on thin multilayered metamaterials

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Abstract

Light absorption plays an important role in many research areas. Here, we propose and demonstrate a thin ultra-broadband strong light absorber consisting of periodic taper arrays constructed by an alumina-chrome multilayered metamaterial (MM) on a gold substrate. The large material loss of chrome and special anisotropic effective permittivity of the MM are the fundamental origins of the ultra-broadband absorption in which no resonance is used. The absorber is lowly sensitive to the incident angle, and can be insensitive to the polarization. One two-dimensional periodic array of 400nm-height MM tapers is fabricated. The measured absorption can be over 90% almost over the entire solar spectrum, reaching an average level of 96%, and it remains high (above 85%) even in the longer wavelength range until 4 μ m. The proposed absorbers open a new avenue to realize broadband thin light-harvesting structures.

Light absorption is key important in many fields of science and modern technologies, e.g., photon detection, thermal radiation, collection of solar energy, and photochemistry¹⁻³. Broadband light absorption is important and interesting, but it is also a challenge. Traditionally, tapered micro-structures^{4,5} made of single materials or bulky low-density materials⁶⁻⁸ are widely adopted. This is generally at the cost of the structure thickness, and the absorbers are often optically thick. Absorbers consisting of low-density materials, such as semiconductors⁶ and carbon nanotubes^{7,8}, are sparse and fragile.

Recently, metamaterials have gained extensive and intense attention. They can realize unusual effective electromagnetic material parameters, such as negative index^{9,10}, zero index¹¹, and hyperbolic anisotropy¹². And many exotic phenomena and applications, not easily achievable using naturally occurring materials, have been disclosed and justified, such as superlens¹³, cloaking¹⁴ and anomalous reflection and refraction^{15,16}. Metamaterials also provide new approaches to control wave absorption with several advantages including thin structure thickness, flexible wavelength scalability, and angle or polarization insensitivity¹⁷⁻²⁴. Optical metamaterial absorbers have already been experimentally demonstrated^{21,23,24}. However, metamaterial absorbers usually only possess narrow absorption bandwidth, because they depend on the electric and magnetic resonance of their subwavelength units, similar to the common narrowband absorption based on grating or microcavity coupling²⁵⁻³⁰. To extend the bandwidth, blending several different resonators operating at several neighboring frequencies into one unit has been adopted²⁰⁻²³, but the bandwidth cannot be broadened significantly because the number of blended resonators is limited. In addition, broadband light absorption has also been explored by embedding metal nanoparticles in dielectric materials, but the bandwidth is still limited and cover only a part of the solar spectrum^{31,32}.

Here, we will demonstrate a novel ultra-broadband absorber covering the entire visible regime, near-infrared regime and even some part of the mid-infrared regime. When a periodic array of tapers is constructed by a multilayered metamaterial (MM) composed of alternating deep-subwavelength metal and dielectric layers, two

mechanisms contribute to the ultra-broadband absorption together, which do not depend on resonance. One is that the incident light in the long wavelength range is strongly absorbed by a slow-wave effect. Based on this effect, some of the authors have suggested theoretically a mid-infrared ultra-broadband MM absorber³³, but if it is directly scaled to work at higher frequencies covering the solar spectrum, the structure parameters will be rather rigorous and limit practical fabrication. The other one is that the MM tapers are equivalent to anisotropic dielectric tapers with high loss in the short wavelength range. The suggested absorber is thin enough compared with the working wavelength range. Its fabrication process is feasible, and a realized sample will be shown to possess good absorption performance.

We firstly investigated a periodic structure composed of alternating dielectric and metal layers demonstrated in Figure 1a. The permittivity and thickness of the dielectric layers are ϵ_d and t_d , respectively, and ϵ_m and t_m for the metal layers. When the dielectric and metal layers possess subwavelength thickness and the thickness of the metal layer is smaller than its penetration depth, the periodic structure can be homogenized as a MM with effective anisotropic permittivity ϵ_{mm} . According to the effective medium theory³⁴, the components of ϵ_{mm} can be written as

$$\begin{aligned}\epsilon_x = \epsilon_y &= f \cdot \epsilon_m + (1-f) \cdot \epsilon_d \\ \epsilon_z &= \frac{\epsilon_m \cdot \epsilon_d}{f \cdot \epsilon_d + (1-f) \cdot \epsilon_m}\end{aligned}\tag{1}$$

where $f = t_m/(t_m + t_d)$ is the metal filling ratio. MMs enable an effective way for molding out some special useful permittivity. When $\text{Re}(\epsilon_x)$ and $\text{Re}(\epsilon_y) < 0$ or $\text{Re}(\epsilon_z) < 0$, the equal-frequency dispersion curve of a MM is hyperbolic, for which several interesting applications have been proposed, such as hyperlens^{35,36} and enhancement of spontaneous emission³⁷.

Here, the dielectric layers are made up of alumina (Al_2O_3) with $t_d=70\text{nm}$, and the metal layers are made up of chrome (Cr) with $t_m=10\text{nm}$. The permittivity parameters of Al_2O_3 and Cr are taken from Ref. 38, and the permittivity of Cr is shown in Figure 1c. Figure 1d shows the real and imaginary parts of ϵ_{mm} calculated with Eq. (1). In this

paper, $\exp(-i\omega t)$ is adopted as the time harmonic factor.

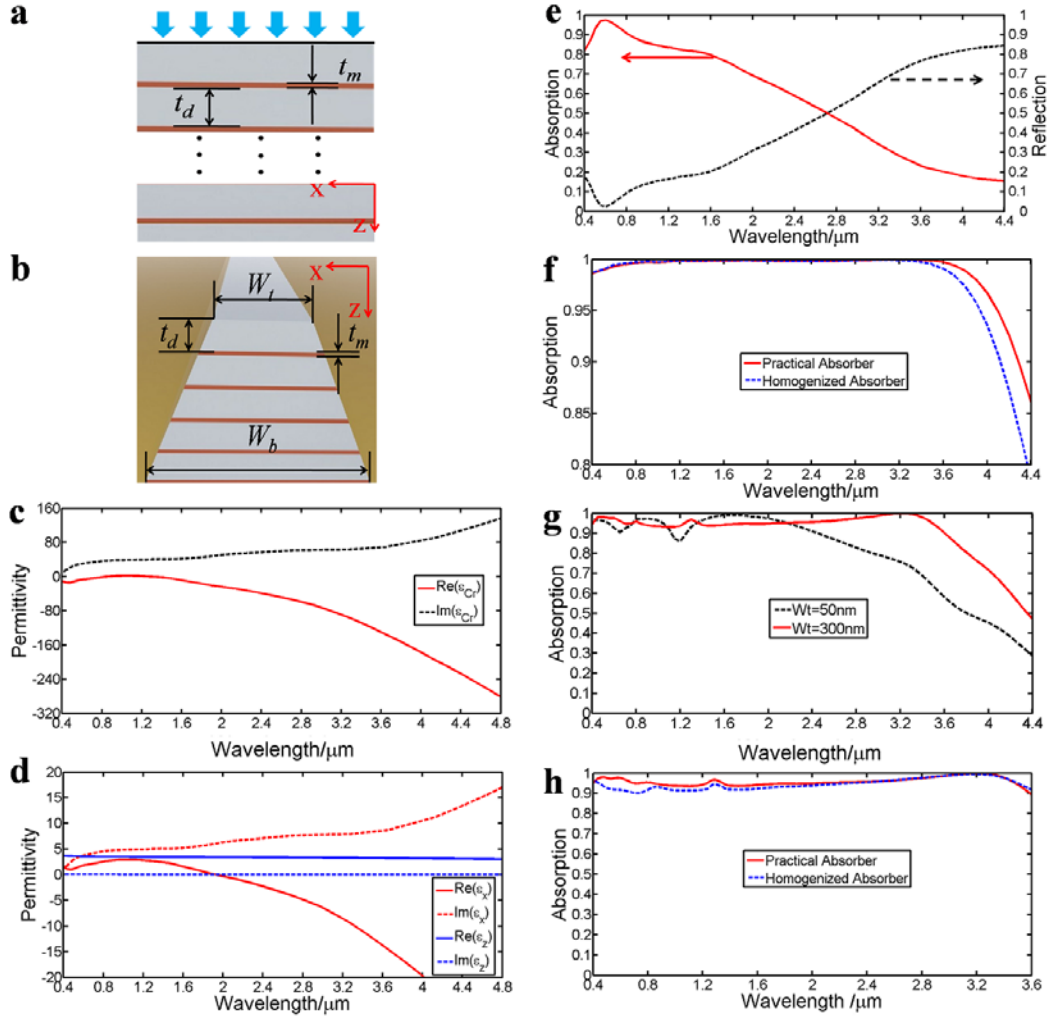


Figure 1. (a) Semi-infinite MM. (b) Unit cell of a MM taper absorber with a gold substrate. $t_d=70nm$, $t_m=10nm$. (c) Permittivity of Cr. (d) Components of ϵ_{mm} calculated with Eq. (1) for the MM. (e) Absorption (red solid line) and reflection (black dashed line) for the semi-infinite MM. (f) Absorption of a MM taper absorber with $W_t=50nm$, $W_b=750nm$, $P_x=800nm$, and $H=1600nm$. The absorption is represented by the red solid line when the MM is not homogenized, and by the blue dashed line when the MM is homogenized. (g) Absorption of a MM taper absorber with $W_b=750nm$, $P_x=800nm$, and $H=400nm$. The black dashed line is for $W_t=50nm$, and the red solid line for $W_t=300nm$. (h) Absorption of a MM taper absorber with $W_t=300nm$, $W_b=750nm$, $P_x=800nm$, and $H=400nm$. The absorption is represented by the red solid line when the MM is not homogenized, and by the blue dashed line when the MM is

homogenized. In (e)–(h), the TM polarized light impinges normally on the structures.

The MM provides us a feasible effective lossy material prominent for light absorption. When the MM is semi-infinite, the normal reflection is shown in Figure 1e. If it is not specified out in the following of this paper, it is assumed a plane wave of TM polarization is incident downwards as an excitation source, which means that the incident plane is the x - z plane and the magnetic field is polarized along the y axis (so ε_y does not work in such a case and will not be included in the discussion for simplicity). In the short-wavelength range, the reflection is low but still obvious, and in the long-wavelength range, the reflection is strong since the MM acts as an effective anisotropic plasmonic material. In order to reduce the reflection, as shown in Figure 1b, a one-dimensional (1D) periodic array of MM tapers is constructed on a gold (Au) substrate. As an example, it is first investigated when the transverse period is $P_x=800nm$, the top width, bottom width, and total height of each taper are $W_t=50nm$, $W_b=750nm$, and $H=20(t_m+t_d)=1600nm$ (20 pairs of Al_2O_3 and Cr layers), separately. In simulation, the finite-difference time-domain method (FDTD) is used³⁹, and the finite element method is also used as verification⁴⁰. As shown in Figure 1f, the absorption obtained from the practical parameters of the MM taper array (red solid line) is very close to that as the MM is homogenized (blue dashed line), which indicates that the effective medium theory is valid for the current case. The MM taper array realizes near-unity absorption in an ultra-broad wavelength range, which is induced by two mechanisms as explained in the following.

In the short-wavelength regime, $Re(\varepsilon_x)$ and $Re(\varepsilon_z)$ are positive, which indicates that the MM acts as an anisotropic dielectric material. Thus, the absorption mechanism in this wavelength range is similar to that of a taper array made of common lossy dielectric. It is well known that the reflection can be eliminated thoroughly if the common lossy dielectric tapers are high enough^{41,42}. The MM possesses large loss in a wide short-wavelength range, so strong broadband absorption can be obtained. As $Im(\varepsilon_x)$ is large but not much greater than $Re(\varepsilon_x)$, the MM tapers do not need to be very high for strong absorption. Figure 2a–c show the magnetic field

distributions normalized by the magnetic amplitude of the incident wave at several different wavelengths ($\lambda=0.5\mu\text{m}$, $0.9\mu\text{m}$, and $1.3\mu\text{m}$), and Figure 2d–f show the corresponding normalized electric field distributions. The magnetic field is localized inside the tapers, and the electric field is localized on the side surfaces, which means that the incident light energy is mainly absorbed there. As the wavelength increases, the magnetic and electric field patterns enlarge gradually, but are kept on the upper part of the MM tapers. This is similar to that in common lossy dielectric tapers.

In the long-wavelength regime, the MM tapers can neither be treated as dielectric tapers, nor as common metal tapers since $\text{Re}(\epsilon_x)$ and $\text{Re}(\epsilon_z)$ possess opposite signs. As stated in Ref. 33, the broadband absorption arises from a slow-wave effect. The MM tapers can be treated as tapered hyperbolic waveguides. For a guided mode at some frequency, when it propagates downward along a MM taper gradually toward some critical width, it is slowed down and blocked. Due to large loss, the guided mode is strongly absorbed. The incident light can efficiently excite these modes and then be strongly absorbed in a wide long-wavelength range. For better demonstrating this absorbing mechanism, the normalized magnetic field distributions at several different wavelengths ($\lambda=2\mu\text{m}$, $3\mu\text{m}$, and $4\mu\text{m}$) are shown in Figure 2g–i, and the corresponding normalized electric field distributions are shown in Figure 2j–l. Similar to that in the short-wavelength range, the magnetic field is also localized inside the MM tapers and the electric field is localized on the side surfaces. However, it is identified that the incident light at a different wavelength accumulates at a different position of the MM tapers. For instance, the incident light at $\lambda=2\mu\text{m}$ is trapped mainly at the upper part of the tapers, and the magnetic and electric fields at the bottom part are weak. The incident light at $\lambda=3\mu\text{m}$ is localized at the middle waist region of the tapers, and at a longer wavelength, $\lambda=4\mu\text{m}$, the incident light is mainly harvested at the bottom part of the tapers. The shift of the field localization follows the shift of the position at which a guided mode is blocked.

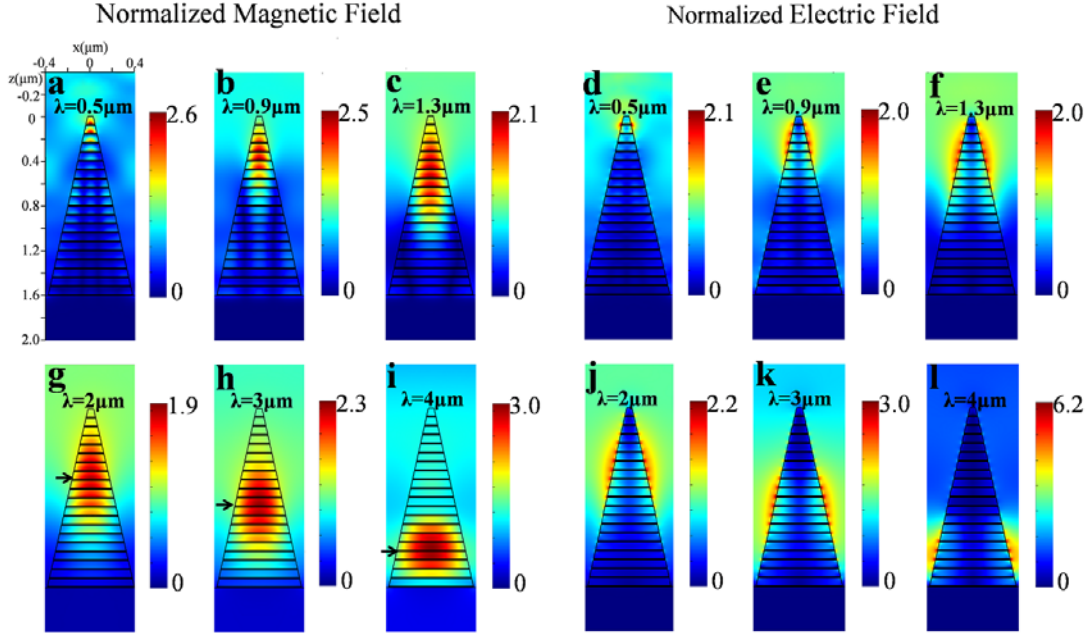


Figure 2. Normalized magnetic and electric field distributions of a MM taper absorber: (a)–(c) and (g)–(i) normalized magnetic field distributions at different incident wavelengths, and (d)–(f) and (j)–(l) corresponding normalized electric field distributions. The MM taper absorber is the same as that in Figure 1f.

To pursue perfect absorption, relatively high MM tapers are used in the above. In fact, the MM tapers can be cut down to get a thinner absorber which can be fabricated more easily while strong absorption is preserved. When $H=400nm$ (5 pairs of Al_2O_3 and Cr layers) with the other parameters fixed, the normal reflection is a bit large because of the fast transition from the top to the bottom of the tapers, and the absorption is decreased especially in the long-wavelength range (black dashed line in Figure 1g). To optimize the reflection in the wide wavelength range, W_t is enlarged to $300nm$ now. The obtained absorption is shown in Figure 1g (red solid curve), and the reflection can be tolerated. To demonstrate the validity of the effective medium theory, the absorption is also shown in Figure 1h (blue dashed curve) when the MM is homogenized, and little change is brought. The normalized magnetic field distributions at different wavelengths are shown in Figure 3. Comparing Figure 3 and Figure 2, one can see that the absorbing behavior changes little in the

short-wavelength range, but obviously in the long-wavelength range. As indicated in Figure 3, the field patterns are not localized inside a very small volume in the long-wavelength range, but diffuse into several dielectric and metal layers nearby. When the height of the tapers is reduced to 400nm from 1600nm, the field patterns cannot be squeezed in size correspondingly, and there is not enough space to accommodate them. Consequentially, the accumulation patterns are blocked and disturbed by the gold substrate, and mainly localized at the bottom of the tapers at long wavelengths. However, although there is disturbance, strong absorption is kept.

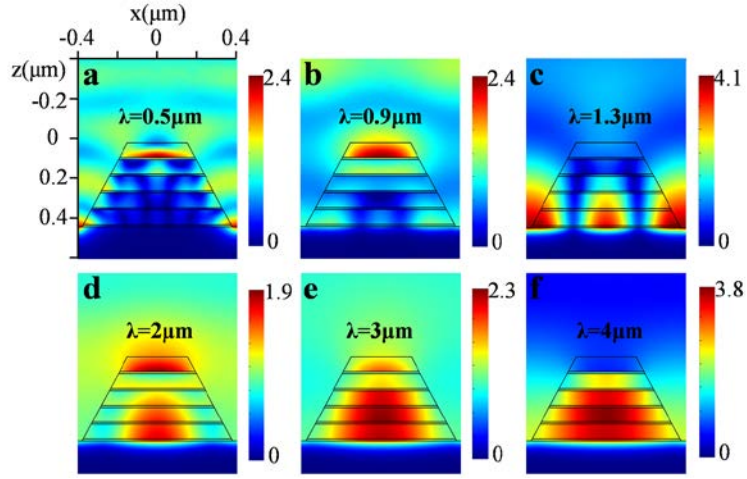


Figure 3. Normalized magnetic field distributions at different incident wavelengths. The MM taper absorber is the same as that in Figure 1h.

In the absorption process, the Au substrate is necessary. If it is removed, a small part of the incident wave will transmit through the absorber structure and the absorption effect will be weakened, especially in the long-wavelength range. Since Au is lossy, it can partially absorb the incident light. By a simple equation of $P_{abs} = \omega \epsilon'' E^2$ integrated over some material volume, where ω is the angular frequency, ϵ'' is the imaginary part of the permittivity, and E is the electric field amplitude, one can obtain the part of the incident wave absorbed by different materials. The absorption of the Cr layers and the Au substrate normalized by the incident power is shown in Figure 4. The absorption of the Cr layers dominates the total absorption in the whole investigated wavelength range while the absorption in the Au substrate is

weak. This indicates that the Au substrate mainly work as a reflection mirror and contributes little to the direct absorption of the incident light, which is consistent with the previous qualitative discussion. There are two obvious absorption peaks on the absorption curve of the Au substrate. The absorption peak at $\lambda=500nm$ is attributed to the intrinsic high loss of Au at this wavelength, and the peak around $\lambda=1300nm$ is due to the excitation of surface plasmon on the Au surface (see Figure 3c).

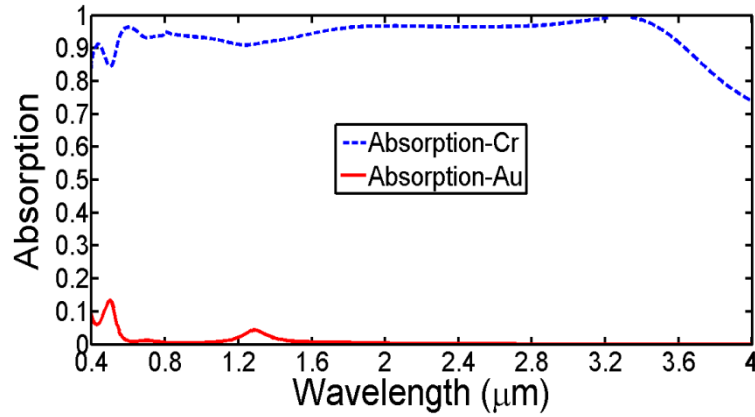


Figure 4. Power absorbed by the different materials in a MM taper absorber. The power is normalized by the incident power. The MM taper absorber is the same as that used in Figure 1h.

In the above, the 1D MM taper array is polarization dependent. To remove this dependence, a two-dimensional (2D) periodic array of MM tapers (quadrangular frustum pyramids) is proposed, which is illustrated in Figure 5a. To verify the absorption conception, it is relatively easy to experimentally fabricate a 2D absorber of MM tapers with 5 pairs of Al_2O_3 and Cr layers on a $200nm$ -thick Au film, which is illustrated in Figure 5c. The Au substrate is thick enough to block the transmission in the entire investigated spectrum. The period along the x axis is the same as that along the y axis, and the structure parameters are identical to those of the 1D MM taper absorber used in Figure 1h.

The 2D taper array ($12\mu m \times 12\mu m$) is fabricated by milling a planar dielectric-metal multilayered structure with the focused-ion-beam (FIB) technology

(the details are given in the Supporting Information). A group of parallel grooves first needs to be milled out and the corresponding scanning electron microscopy (SEM) image is shown in Figure 5b. Then another group of parallel grooves along the y axis is milled out to implement the 2D MM taper array. With proper design, a 2D MM taper array is fabricated successfully as shown in Figure 5c.

The total reflection of the fabricated sample in the visible and near-infrared regimes is measured using a homemade linear reflection spectroscopy setup equipped with an inverted microscope, a super-continuum source, and several polarizers and spectrometers (the details are given in the Supporting Information). Because of the limited response of the polarizers, we can only measure the absorption performance in the wavelength range between 400nm and 2100nm . And due to the limited response of the spectrometers, measurement is not made in the wavelength range between 900nm and 1000nm . The reflection spectrum in the mid-infrared regime (above 2500nm) is measured using a Thermo Scientific Nicolet iN10 Fourier-transform infrared (FTIR) microscope in which the light source is not polarized. It is impressive that the measured absorption is above 90% in the entire solar spectrum, reaching an average level of 96%, and remains high (above 85%) even in the longer wavelength range until $4\mu\text{m}$ (see the dashed black curve in Figure 5d). To our best knowledge, this is the recorded broadband absorption reported for thin absorbers at visible and infrared frequencies experimentally. Comparing the simulated and experimental absorption curves in Figure 5d, there is remarkably good agreement between the measured and simulated results if taking into account the imperfection in the fabricating process as well as the measurement error. To verify the symmetry degree of the fabricated 2D MM taper array, the absorption performance for two orthogonal polarizations (the normally incident light is polarized along the x or y axis) is also measured in the wavelength range between 400nm and 2100nm . In Figure 5e, one can see that the measured absorption spectra for two polarizations display small difference, almost negligible in the short wavelength range, which manifests the good symmetry of the fabricated sample.

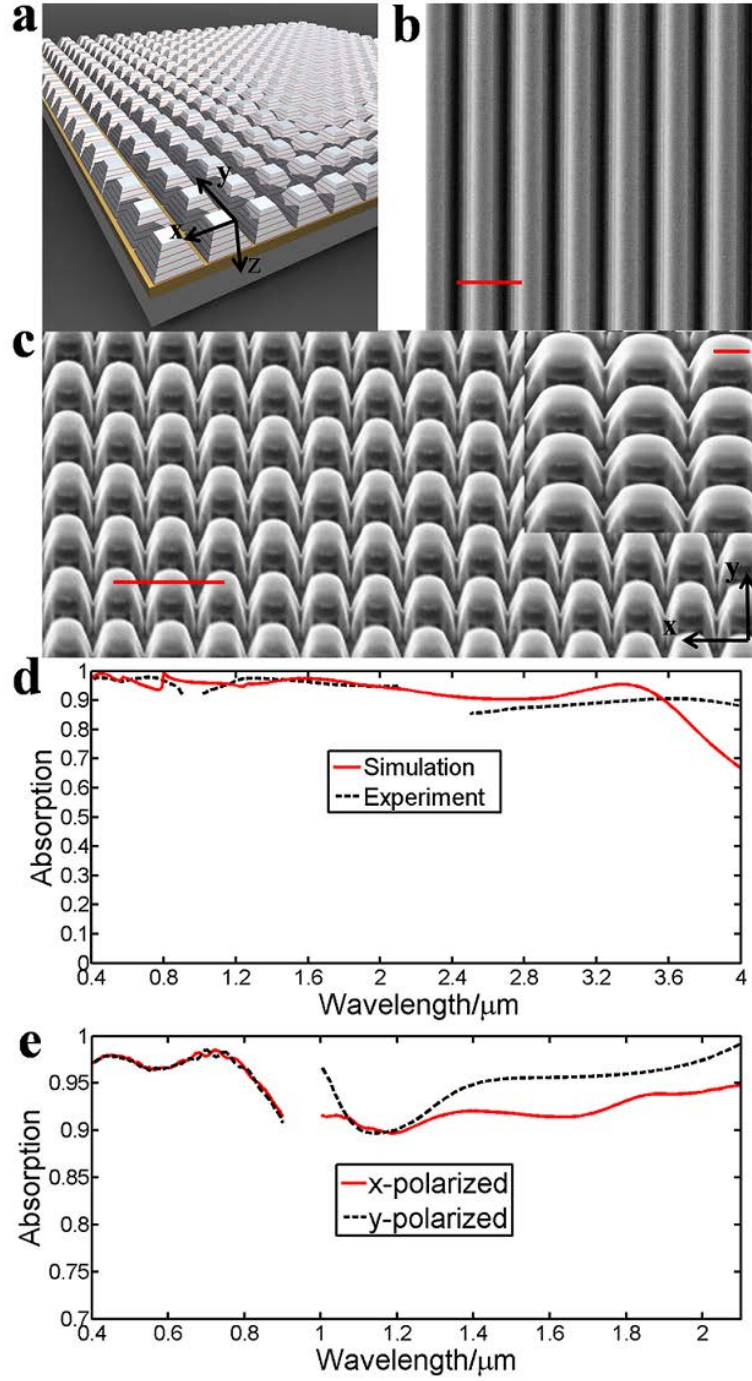


Figure 5. (a) Schematic of the 2D MM taper absorber. $t_d=70nm$, $t_m=10nm$, $W_t=300nm$, $W_b=750nm$, and $P_x=P_y=800nm$. (b) SEM image of 1D grooves (scale bar $1\mu m$) milled out in a multilayered film. (c) SEM image of the 2D MM taper array (scale bar $2\mu m$). Local magnification is shown in the inset (scale bar $300nm$). (d) Comparison between the experimental absorption (black dashed line) and simulated absorption (red solid line). The normally incident light is not polarized. (e) Absorption spectra for two orthogonal polarizations. The normally incident light is polarized along the x axis (red

solid line) or y axis (black dashed line).

In the above, the incident light impinges normally on the 2D MM absorber both in the simulation and experiment. According to the two absorption mechanisms, the absorption should be lowly sensitive to the incident angle (θ). For the sake of convenience, TM polarization (the magnetic field of the incident light is kept parallel to the y axis) is just taken as an example (Fig. 6a). Simulation is performed to verify the angular dispersion of the absorption at various incident angles which is shown in Figure 6b. In the simulation, θ is varied from 0 degrees to 80 degrees in steps of 5 degrees. The absorption is not sensitive to θ . The ultra-broadband absorption response can be achieved when θ is below 40 degrees, and the absorption still remains above 70% even when θ reaches 60 degrees.

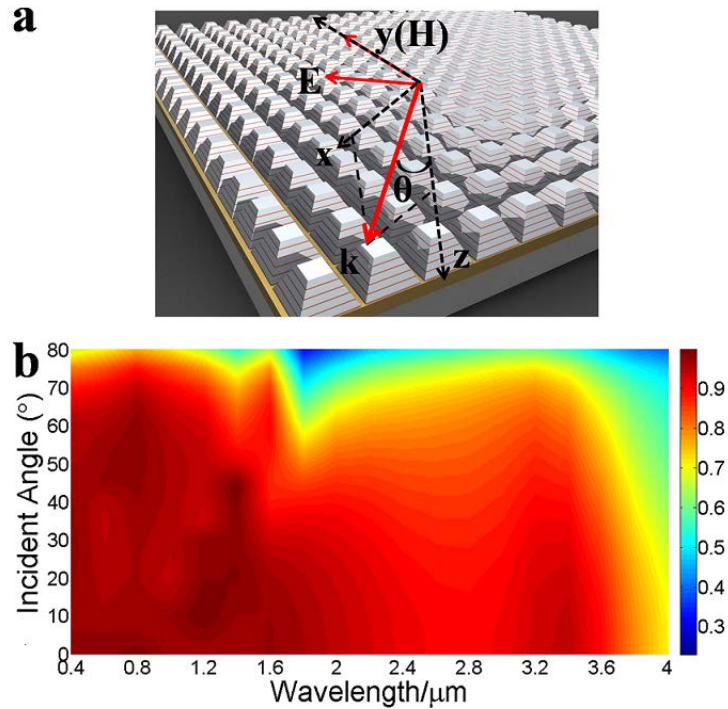


Figure 6. Dependence of the absorption performance on the incident angle: (a) Schematic of the incident angle (θ) for TM polarization, (b) Absorption as a function of the wavelength and incident angle.

In conclusion, we have suggested a thin ultra-broadband nanostructured absorber which can cover the entire visible regime, near-infrared regime and even some part of the mid-infrared regime based on an anisotropic MM. A 2D MM taper absorber has been fabricated, and the measured strong light absorption is exhibited to be broadband on record. Our approach can easily be exploited with other materials, not subjected to chrome/alumina, for example, titanium/tungsten or silica/magnesium fluoride. This may provide a new possible candidate for thermal emission, thermophotovoltaic technology and photochemistry.

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